





#### **N-CHANNEL ENHANCEMENT MODE MOSFET**

#### **Features**

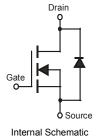
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

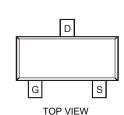
#### **Mechanical Data**

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)









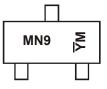
## Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2041L-7	SOT-23	3000/Tape & Reel

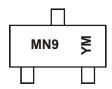
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**







Shanghai A/T Site

MN9 = Product Type Marking Code

YM = Date Code Marking for SAT (Shanghai Assembly/ Test site) YM = Date Code Marking for CAT (Chengdu Assembly/ Test site)

Y or  $\overline{Y}$  = Year (ex: A = 2013)

M = Month (ex: 9 = September)

Date Code Key

Date Code Noy												
Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		X		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characte	eristic		Symbol	Value	Units
Drain-Source Voltage			V <sub>DSS</sub>	20	V
Gate-Source Voltage		V <sub>GSS</sub>	±12	V	
Continuous Drain Current (Note 5) Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I <sub>D</sub>	6.4 4.5	А	
Pulsed Drain Current (Note 6)			I <sub>DM</sub>	30	Α

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P <sub>D</sub>	0.78	W
Thermal Resistance, Junction to Ambient @ T <sub>A</sub> = +25°C	$R_{\theta JA}$	161	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

Notes:

- 5. Device mounted on FR-4 PCB with minimum recommended pad layout.
- 6. Repetitive rating, pulse width limited by junction temperature.

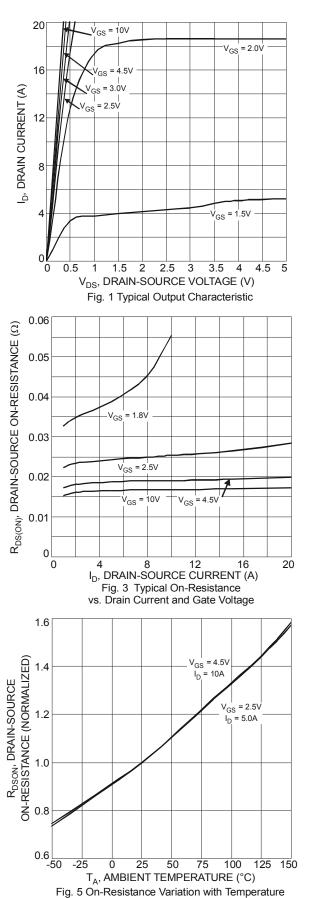
### Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	20	_		V	$V_{GS} = 0V, I_D = 250\mu A$		
Zero Gate Voltage Drain Current T <sub>J</sub> = 25°C	I <sub>DSS</sub>		_	1.0	μΑ	$V_{DS}$ = 20V, $V_{GS}$ = 0V		
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0V		
ON CHARACTERISTICS (Note 7)								
Gate Threshold Voltage	V <sub>GS(th)</sub>	0.5	_	1.2	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$		
Static Drain-Source On-Resistance	0	_	20	28	mΩ	$V_{GS} = 4.5V$ , $I_D = 6.0A$		
Static Dialii-Source Off-Resistance	R <sub>DS (ON)</sub>		26	41	11122	$V_{GS} = 2.5V$ , $I_D = 5.2A$		
Forward Transfer Admittance	Y <sub>fs</sub>	_	6	_	S	V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A		
Diode Forward Voltage	$V_{SD}$	_	0.7	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.7A		
DYNAMIC CHARACTERISTICS (Note 8)						_		
Input Capacitance	C <sub>iss</sub>		550	-		V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1.0MHz		
Output Capacitance	Coss	-	88	_	pF			
Reverse Transfer Capacitance	C <sub>rss</sub>	_	81	_				
Gate Resistance	$R_g$	_	1.34	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$		
Total Gate Charge (10V)	$Q_g$	_	15.6	_	nC	$V_{GS} = 10V, V_{DS} = 10V, I_D = 6A$		
Total Gate Charge (4.5V)	$Q_g$	_	7.2	_		V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 10V, I <sub>D</sub> = 6A		
Gate-Source Charge	$Q_{gs}$	_	1.0	_	nC			
Gate-Drain Charge	$Q_{gd}$	_	1.9	_				
Turn-On Delay Time	t <sub>D(on)</sub>	_	4.69	_		V <sub>DD</sub> = 10V, V <sub>GEN</sub> = 4.5V,		
Turn-On Rise Time	t <sub>r</sub>	_	13.19	_				
Turn-Off Delay Time	t <sub>D(off)</sub>	_	22.10	_	ns	$R_{GEN} = 1\Omega$ , $I_D = 6.7A$		
Turn-Off Fall Time	t <sub>f</sub>	_	6.43	_				

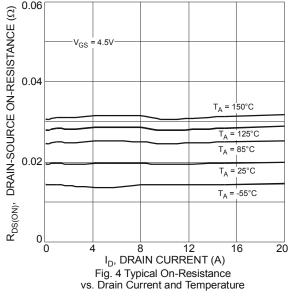
Notes:

- 7. Short duration pulse test used to minimize self-heating effect.
- 8. Guaranteed by design. Not subject to production testing.





20 V<sub>DS</sub> = 5V 16 (<del>V</del>) LN 12 8 T<sub>A</sub> = 150°C T<sub>A</sub> = 25°C T<sub>A</sub> = 35°C T<sub>A</sub> = 35°C T<sub>A</sub> = 35°C



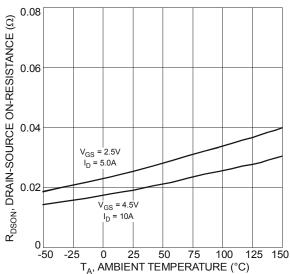
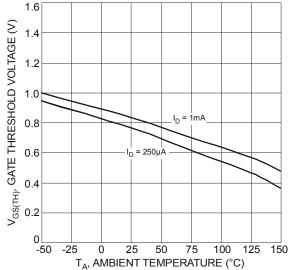
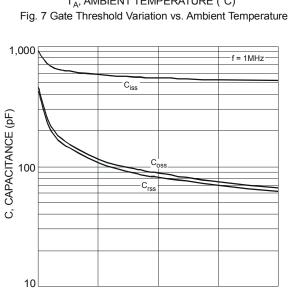


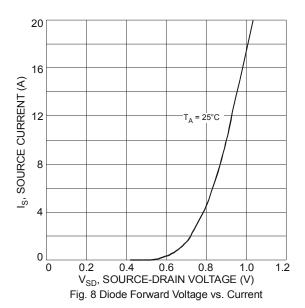
Fig. 6 On-Resistance Variation with Temperature







V<sub>DS</sub>, DRAIN-SOURCE VOLTAGE (V) Fig. 9 Typical Total Capacitance



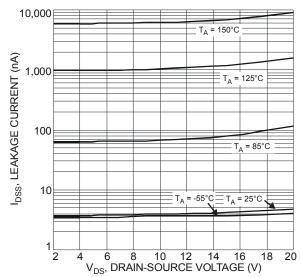
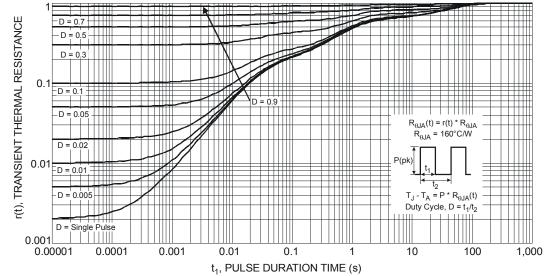


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage



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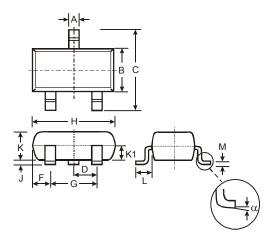
Fig. 11 Transient Thermal Response

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# **Package Outline Dimensions**

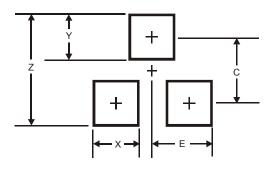
 $Please see AP02002 \ at \ http://www.diodes.com/datasheets/ap02002.pdf \ for \ the \ latest \ version.$ 



	SOT-23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	1	1	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All	All Dimensions in mm							

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
Е	1.35



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